

# Schottky Barrier Diode Die Specification

Schottky barrier diode die based on silicon planar process  
 100SS-280A

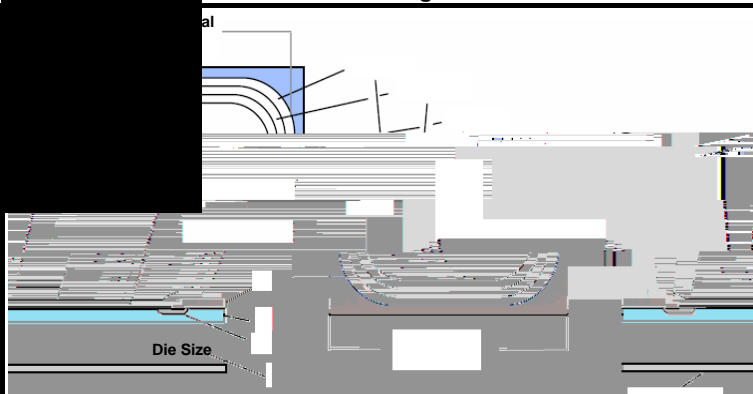
## Characteristics

Parameter	Symbol	Rating
Reverse voltage	$V_{RRM}$	100 V
Forward current	$I_{F(AV)}$	2 A
Forward current (surge, 1 cycle)	$I_{FSM}$	50 A
Storage temperature range	$T_{stg}$	-50 to +175 °C
Junction temperature	$T_j$	175 °C

## Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 1\text{mA}$	$V_{BR}$	105 V	120V
Maximum forward voltage drop $I_F = 2\text{A}$	$V_F$	0.83V	0.80V
Maximum reverse current $V_R = V_{RRM}$	$I_R$	5uA	0.3uA

## Dimensions and Outline Drawing



Die Thickness *	11 Mils
Die Size **	40 Mils
Top Metal Pad	36.5 Mils
Active Area	32.9 Mils
Top Metal	Ag
Back Metal	Ag

Note: 1 \* : Also can offer device with 8 mils thickness  
 2 \*\*: Cutting street width is around 1.5 mils

## Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Manufacturer does not guarantee device performance after assembly.  
 All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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